CLAIMS

1.   (Currently amended) A method of generating an initializing signal for initializing an inner circuit in a semiconductor memory device, the method comprising:

(a) receiving a mode set command for initializing the inner circuit after receiving a precharge command; and

(b) generating a control signal in response to the received mode set command and using the control signal as the initializing signal.

2.   (Original) The method of claim 1, wherein the mode set command is a signal applied to the semiconductor memory device via an external pin.

3.   (Original) The method of claim 1, wherein the mode set command is a mode register set (MRS) command in a synchronous dynamic random access memory (DRAM).

4.   (Original) The method of claim 1, wherein the mode set command is a Write Column address strobe (CAS) Before Row address strobe (RAS) (WCBR) in an asynchronous dynamic random access memory (DRAM).

5.   (Previously presented) A method of generating an initializing signal for initializing an inner circuit in a semiconductor memory device, the method comprising:

(a) receiving a precharge command for precharging the semiconductor memory device;

(b) receiving a mode set command for initializing the inner circuit after receipt of the precharge command; and

(c) generating a control signal in response to the received mode set command, and using the control signal as the initializing signal.

6.   (Original) The method of claim 5, wherein the mode set command is a signal applied to the semiconductor memory device via an external pin.

7.   (Original) The method of claim 5, wherein the mode set command is a mode register set (MRS) command in a synchronous dynamic random access memory (DRAM).

8.   (Original) The method of claim 5, wherein the mode set command is a Write Column address strobe (CAS) Before Row address strobe (RAS) (WCBR) in an asynchronous dynamic random access memory (DRAM).